

WHAT IS CLAIMED IS:

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1. A semiconductor device comprising:  
a semiconductor chip having a circuit  
block, a power supply line and a ground line; and  
a condenser chip in which a noise  
reduction condenser connected to said circuit block  
is formed,  
wherein said condenser chip is stacked on  
said semiconductor chip.

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2. The semiconductor device as claimed in  
claim 1, wherein a plurality of circuit blocks are  
formed in said semiconductor chip, and said  
condenser chip has a plurality of condensers  
corresponding to said circuit blocks.

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3. The semiconductor device as claimed in  
claim 1, wherein a plurality of circuit blocks are  
formed in said semiconductor chip, and a plurality  
30 of said condenser chips are provided corresponding  
to said circuit blocks.

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4. The semiconductor device as claimed in  
claims 1, wherein said semiconductor chip has a

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first power supply pad provided on a connecting line extending from one of said power supply line and said ground line to said circuit block; and

5       said condenser chip has a second electrode pad connected to the condenser, and the second electrode pad of said condenser chip is electrically connected to the first electrode pad of said semiconductor chip through a bonding wire.

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5. The semiconductor device as claimed in  
claims 1, wherein said semiconductor chip has a  
15      first power supply pad provided on a connecting line  
extending from one of said power supply line and  
said ground line to said circuit block; and  
          said condenser chip has a second electrode  
pad connected to the condenser, and said condenser  
20      chip is connected to the first electrode pad of said  
semiconductor chip by flip chip bonding.

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6. The semiconductor device as claimed in  
claims 1, wherein the noise reduction condenser of  
said condenser chip is formed by a MOS capacity.

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7. The semiconductor device as claimed in  
claims 1, wherein said semiconductor chip has a  
35      third electrode pad other than said first electrode  
pad connected to said circuit block;  
          said condenser chip has a fourth electrode

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pad other than said second electrode pad connected to the condenser; and

5                   an inductor connected to at least one of said power line and said ground line is formed by connecting said fourth electrode pad of said condenser chip and said third electrode pad of said semiconductor chip by a bonding wire.

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8. The semiconductor device as claimed in claim 7, wherein a plurality of said fourth electrode pads of said condenser chip are provided and a plurality of said third electrode pads of said semiconductor chip are provided; and

said inductor is formed by alternately and sequentially connecting said fourth electrode pads of said condenser chip and said third electrode pads of said semiconductor chip by bonding wires.

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9. A semiconductor device comprising: a first semiconductor chip having a circuit block, a power supply line and a ground line; and a second semiconductor chip stacked on said first semiconductor chip, wherein said first semiconductor chip has a first electrode pad separated from a circuit formed within said first semiconductor chip;

said second semiconductor chip has a second electrode pad separated from a circuit formed within said second semiconductor chip; and

an inductor connected to at least one of said power line and said ground line is formed by connecting said first electrode pad of said first semiconductor chip and said second electrode pad of

said second semiconductor chip by a bonding wire.

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10. The semiconductor device as claimed in  
claim 9, wherein a plurality of said first electrode  
pads of said first semiconductor chip are provided  
and a plurality of said second electrode pads of  
said second semiconductor chip are provided; and  
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said inductor is formed by alternately and  
sequentially connecting said first electrode pads of  
said first semiconductor chip and said second  
electrode pads of said second semiconductor chip by  
15 bonding wires.

*Claim A8* >